

Supporting Information

Doped GNR p-n junction as high performance NDR and rectifying device

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Supporting Information Available

Schematic diagram of the device constructed by sandwiching p-n junction diode in between two gold surfaces (Fig. S1) and I-V characteristics of the device (Fig. S2).

This material is available free of charge via the Internet at <http://pubs.acs.org/>.

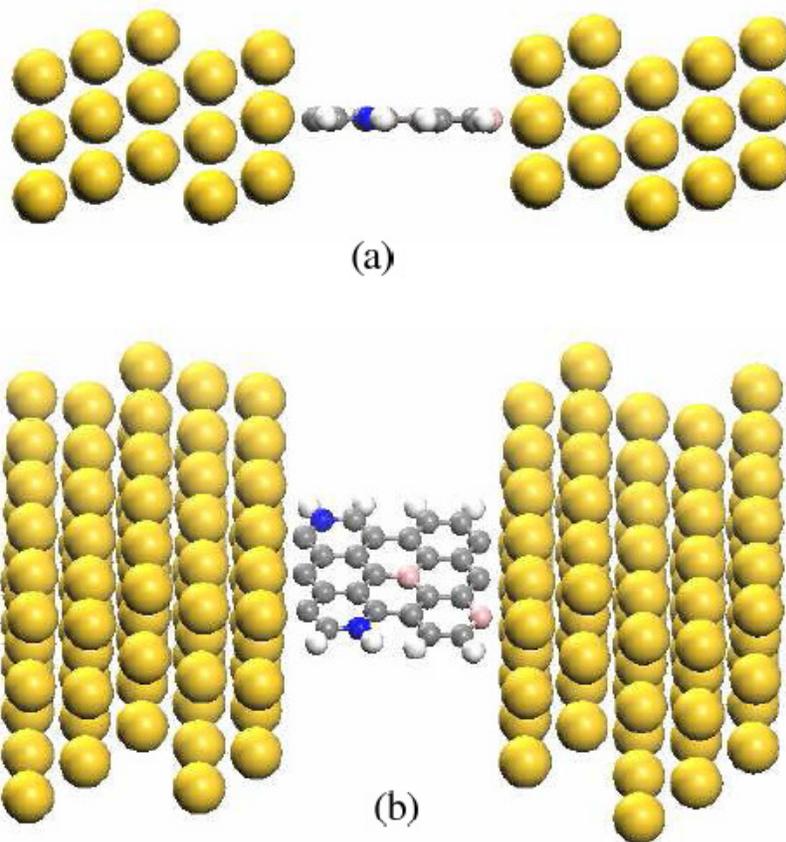


Figure S1: Schematic diagram of the device consisting p-n junction diode (2N, 2B-doped 3.5×2 aGNR) sandwiched in between two Au(111) surfaces, (a) side view and (b) top view.

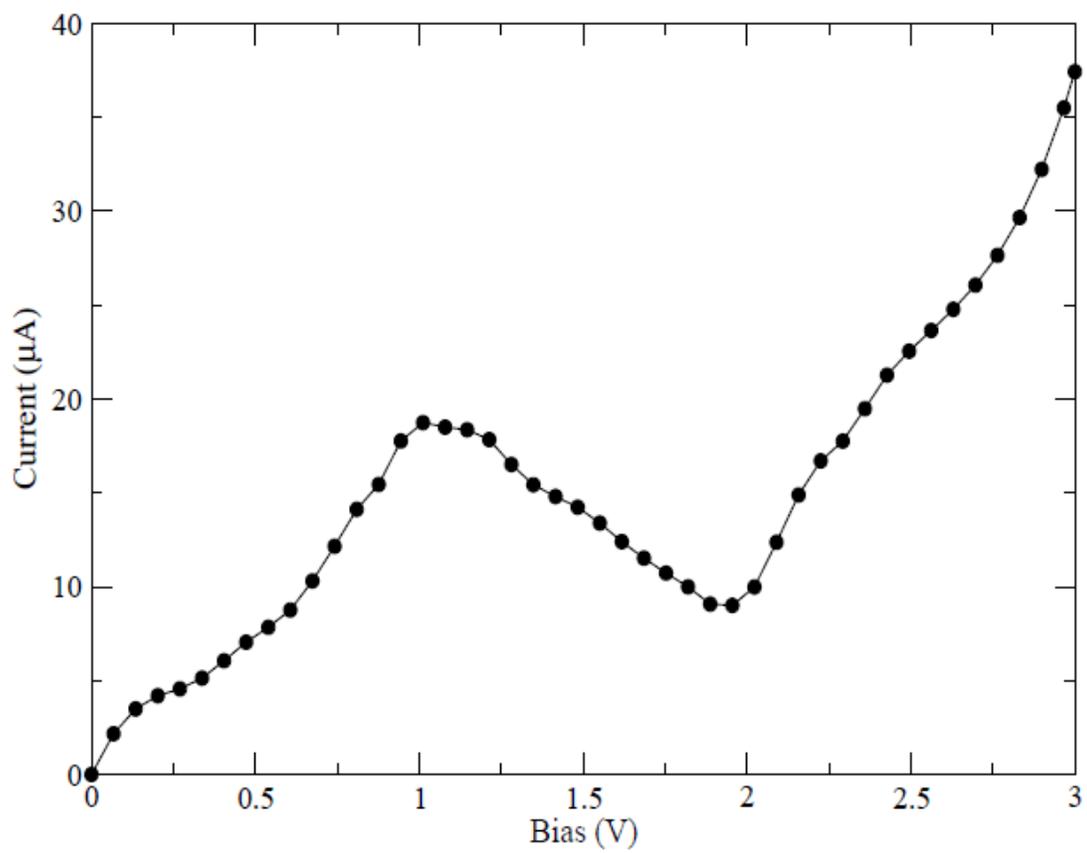


Figure S2: I-V characteristics of p-n junction diode using Au(111) surface as lead.